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DUAL J-FET INPUT OPERATIONAL AMPLIFIER

■ GENERAL DESCRIPTION

These devices are low cost, high speed, dual JFET input operational amplifiers with an internally trimmed input offset voltage. They require low supply current yet maintain a large gain bandwidth product and fast slew rate. In addition, well matched high voltage JFET input devices provide very low input bias and offset currents.

These amplifiers may be used in applicationas such as high speed integrators, fast D/A converters, sample and hold circuits and many other circuits requiring low input offset voltage, low input bias current, high input impedance, high slew rate and wide bandwidth. The devices also exhibit low noise and offsset voltage drift.

■ PACKAGE OUTLINE





8.1M3.53

NJM353M

■ FEATURES

Operating Voltage

 $(\pm 5V \sim \pm 18V)$

• J-FET Input

Low Input Bias Current

(50pA typ.)

High Slew Rate

 $(13V/\mu s typ.)$

• Wide Unity Gain Bandwidth

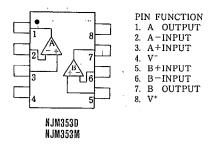
(4MHz typ.)

Package Outline

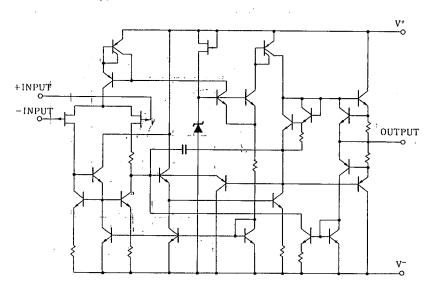
DIP8, DMP8

Bipolar Technology

■ PIN CONFIGURATION



■ EQUIVALENT CIRCUIT (1/2 Shown)



■ ABSOLUTE MAXIMUM RATINGS

(Ta=25℃)

PARAMETER	SYMBOL	RATINGS	UNIT	
Supply Voltage	V*/V-	±18	V	
Differential Input Voltage	V _{ID}	±30	V	
Input Voltage	V _{IC}	±15	V	
Payon Dissination	P _D	(DIP8) 500	mW	
Power Dissipation		(DMP8) 300	mW	
Operating Temperature Range	Topr	-40~+85	r	
Storage Temperature Range	T _{stg}	-40~+125	°C	

(note) For supply voltage less than $\pm 15 \text{V}$, the absolute maximum input voltage is equal to the supply voltage.

■ ELECTRICAL CHARACTERISTICS

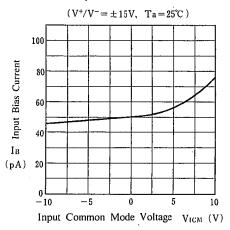
 $(Ta = 25^{\circ}C, V^{+}/V^{-} = \pm 15V)$

PARAMETER	SYMBOL	TEST CONDITION		TYP.	MAX.	UNIT
Input Offset Voltage	V _{IO}	$R_S=10k\Omega$	_	5	10	mV
Average TC of Input Offset Voltage	ΔV ₁₀ /ΔΤ	$R_S = 10k\Omega$	_	10	_	μV/°C
Input Offset Current	I _{IO}		_	25	100	pA
Input Bias Current	IB			50	200	pA
Input Resistance	R _{IN}		_	1012		Ω
Large-signal Voltage Gain	Av	$R_L=2k\Omega$, $V_O=\pm 10V$	88	100		dB
Maximum Peak-to-peak Output Voltage Swing	V _{OM}	$R_{L}=10k\Omega$	±12	±13.5	<u> </u>	v
Input Common Mode Voltage Range	V _{ICM}		±II	+15, -12		v
Common Mode Rejection Ratio	CMR	R _S ≦10kΩ	70	100		dB
Supply Voltage Rejection Ratio	SVR		70	100		dB
Operating Current	I_{CC}		_	3.6	6.5	mA
Channel Separate	CS ⁻	f=1Hz~20kHz		- 120		dB
Slew Rate	SR		_	13	_	V/μs
Unity Gain Bandwidth	fT	·		4	·	MHz
Equivalent Input Noise Voltage	e _n	$R_S = 100\Omega$, $f = 1 \text{ kHz}$		16	_	nV/√ Hz
Equivalent Input Noise Current	in	ſ= lkHz	<u>-</u>	0.01	_	pA/√Hz

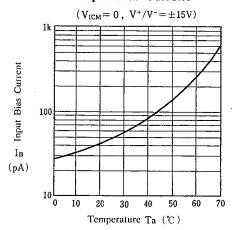
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TYPICAL CHARACTERISTICS

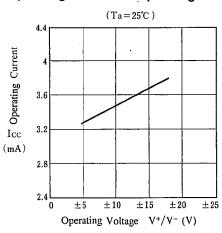
Input Bias Current



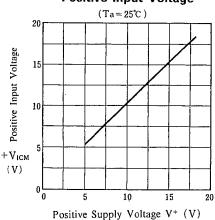
Input Bias Current



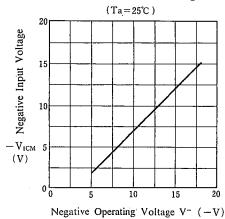
Operating Current vs. Operating Voltage



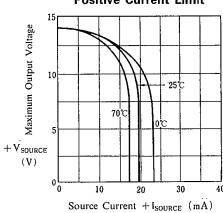
Positive Input Voltage



Negative Input Voltage

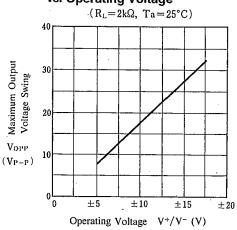


Positive Current Limit

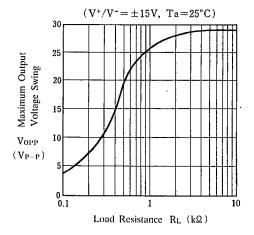


TYPICAL CHARACTERISTICS

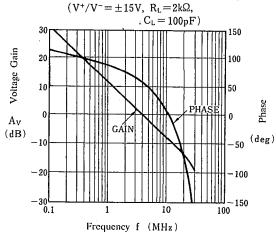
Maximum Output Voltage Swing vs. Operating Voltage



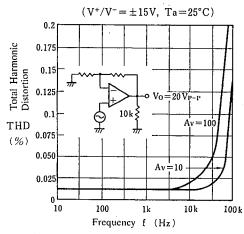
Maximum Output Voltage Swing vs. Load Resistance



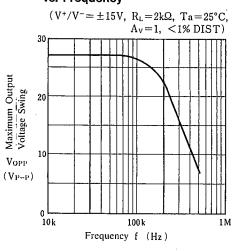
Voltage Gain, Phase vs. Frequency



Total Harmonic Distortion vs. Frequency



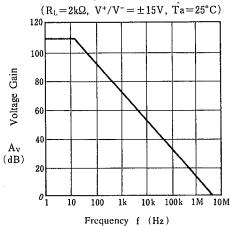
Maximum Output Voltage Swing vs. Frequency



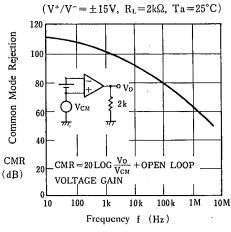
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TYPICAL CHARACTERISTICS

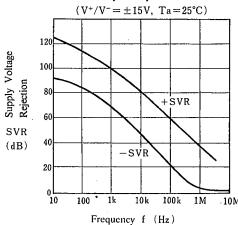
Voltage Gain vs. Frequency



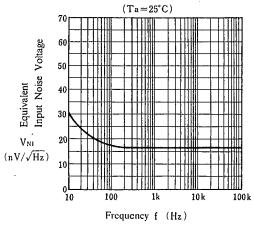
Common Mode Rejection vs. Frequency



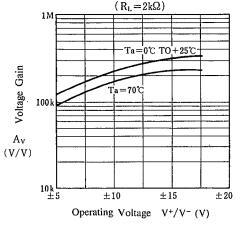
Supply Voltage Rejection vs. Frequency



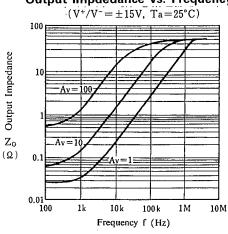
Equivalent Input Noise Voltage vs. Frequency



Voltage Gain vs. Operating Voltage

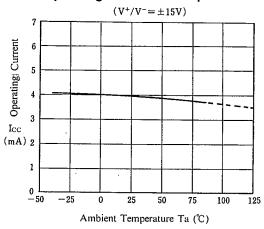


Output Impdedance vs. Frequency

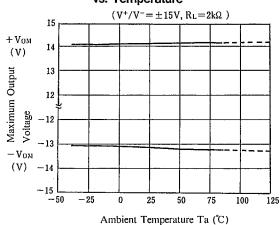


TYPICAL CHARACTERISTICS

Operating Current vs. Temperature

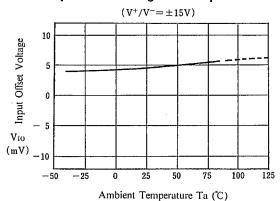


Maximum Output Voltage vs. Temperature



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Input Offset Voltage vs. Temperature



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MEMO

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